UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 6,956,238 B2
DATED : October 18, 2005
INVENTOR(S) : Ryu et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [60], **Related U.S. Application Data**, add -- Application No. 09/834,283, filed on Apr. 12, 2001, now Pat. No. 6,610,366. --.

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, add the following:

-- 6,767,843	07/2004	Lipkin et al.	438/758
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6,133,587	10/2000	Takeuchi et al.	257/77
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6,020,600	02/2000	Miyajima et al.	257/76
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Title page (cont'd),
FOREIGN PATENT DOCUMENTS, add the following:

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EP	1 058 317 A2	12/2000	
JP	01117363	05/1989	Abstract
JP	03034466	02/1991	Abstract
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Baliga, Power Semiconductor Devices, Chapter 7, PWS Publishing, 1996

Bhatnagar et al. "Comparison of 6H-SiC, 3C-SiC, and Si for Power Devices," *IEEE Transactions on Electron Devices*, Vol. 40, No. 3, March 1993, pp. 645-55.

Chung et al., "The Effect of Si:C Source Ratio on SiO_2/SiC Interface State Density for Nitrogen Doped 4H and 6H-SiC," *Materials Science Forum*. (2000) Vols. 338-342, pp. 1097-1100.

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Rao et al. "P-N Junction Formation in 6H-SiC by Acceptor Implantation into N-Type Substrate," Nuclear Instruments and Methods in Physics Research B. vol. 106, 1995, pp. 333-338.

Rao et al. "Al and N Ion Implantations in 6H-SiC," Silicon Carbide and Related Materials. 1995 Conf, Kyoto, Japan. Published 1996.

Capano, M.A., et al., Ionization Energies and Electron Mobilities in Phosphorus–and Nitrogen-Implanted 4H-Silicon Carbide, IEEE ICSCRM Conference 1999, Research Triangle Park, North Carolina (Oct. 10-13, 1999).

Patel, R., et al., Phosphorus-Implanted High-Voltage N.sup.+ P 4H-SiC Junction Rectifiers, Proceedings of 1998 International Symposium on Poer Semiconductor Devices & ICs, pp. 387-390 (Kyoto).

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OTHER PUBLICATIONS,
"Lai et al.", reference, should read -- "Interface Properties of N_2O-Annealed --.

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 24,
Line 15, should read -- interface state density of less than $10^{12}eV^{-11}cm^{-2}$ for --.

Signed and Sealed this

Eighth Day of August, 2006

JON W. DUDAS
Director of the United States Patent and Trademark Office